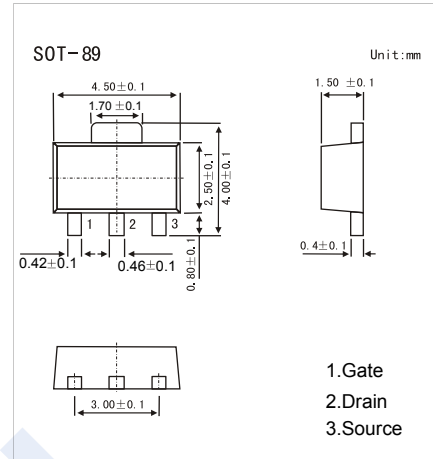
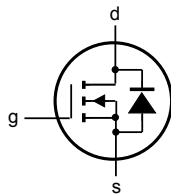


## N-Channel MOSFET

### BSS87 (KSS87)

#### ■ Features

- $V_{DS} = 200V$
- $I_D = 0.28 A$  ( $V_{GS} = 10V$ )
- $R_{DS(ON)} < 6 \Omega$  ( $V_{GS} = 10V$ )
- High-speed switching
- No secondary breakdown.



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	200	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	0.28	A
Pulsed Drain Current	$I_{DM}$	1.1	
Power Dissipation	$P_D$	1	W
Thermal Resistance.Junction- to-Ambient	$R_{thJA}$	125	$^\circ C/W$
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-65 to 150	

#### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D=250 \mu A, V_{GS}=0V$	200			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$			0.2	uA
		$V_{DS}=200V, V_{GS}=0V$			60	
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=1mA$	0.8		2.8	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=0.4A$			6	$\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=25V, I_D=0.4A$		350		mS
Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=25V$			60	pF
Output Capacitance	$C_{oss}$				25	
Reverse Transfer Capacitance	$C_{rss}$				10	
Turn-On DelayTime	$t_{d(on)}$	$V_{GS}=0 \text{ to } 10V, V_{DS}=50V, I_D=250mA$			10	ns
Turn-Off DelayTime	$t_{d(off)}$				25	

#### ■ Marking

Marking	KA
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## N-Channel MOSFET BSS87 (KSS87)

### ■ Typical Characteristics

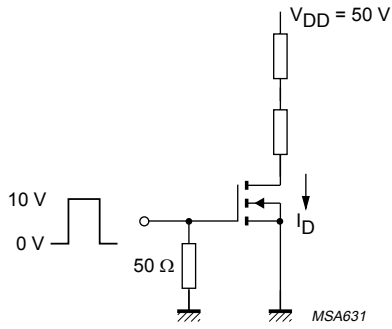


Fig.1 Switching times test circuit.

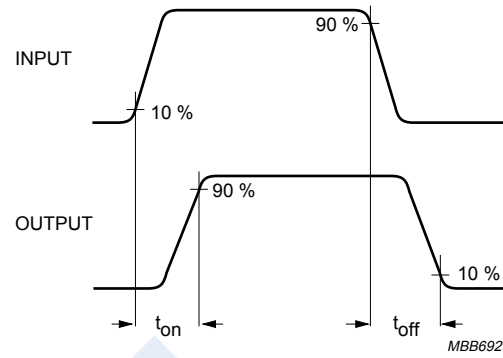


Fig.2 Input and output waveforms.